

N-channel TrenchMOS SiliconMAX standard level FET Rev. 02 — 16 December 2010 Product de

Product data sheet

Product profile 1.

1.1 General description

SiliconMAX standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Higher operating power due to low thermal resistance
- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

DC-to-DC converters

Switched-mode power supplies

1.4 Quick reference data

Table 1.	Quick reference data					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	-	150	V
I _D	drain current	T _{mb} = 25 °C	-	-	55.5	А
P _{tot}	total power dissipation		-	-	250	W
Static cha	aracteristics					
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 25 A; T_j = 25 °C	-	24	30	mΩ
Dynamic	characteristics					
Q_{GD}	gate-drain charge	V _{GS} = 10 V; I _D = 55.5 A; V _{DS} = 120 V; T _j = 25 °C	-	38	50	nC

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2. Pinning information

Table 2.	Pinning	j information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		_
2	D	drain	mb	
3	S	source		
mb	D	mounting base; connected to drain		mbb076 S

SOT78 (TO-220AB)

3. Ordering information

Table 3.Ordering information

Type number	Package		
	Name	Description	Version
PSMN030-150P	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

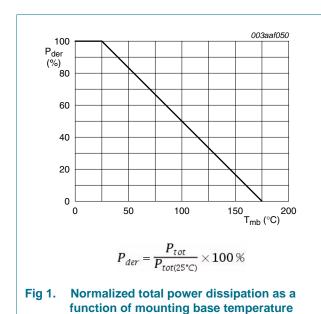
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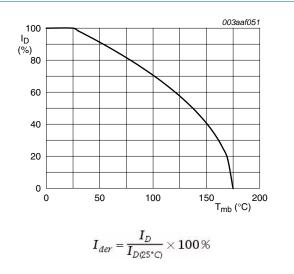
4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C	-	150	V
V _{DGR}	drain-gate voltage	T _j ≥ 25 °C; T _j ≤ 175 °C; R _{GS} = 20 kΩ	-	150	V
V _{GS}	gate-source voltage		-20	20	V
I _D	drain current	T _{mb} = 100 °C	-	39	А
		T _{mb} = 25 °C	-	55.5	А
I _{DM}	peak drain current	pulsed; T _{mb} = 25 °C	-	222	А
P _{tot}	total power dissipation	T _{mb} = 25 °C	-	250	W
T _{stg}	storage temperature		-55	175	°C
Tj	junction temperature		-55	175	°C
Source-drain	diode				
I _S	source current	T _{mb} = 25 °C	-	55.5	А
I _{SM}	peak source current	pulsed; T _{mb} = 25 °C	-	222	А
Avalanche rug	ggedness				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy		-	300	mJ
I _{AS}	non-repetitive avalanche current	$V_{sup} \le 50 \text{ V}; V_{GS} = 10 \text{ V}; T_{j(init)} = 25 \text{ °C};$ R _{GS} = 50 Ω ; unclamped	-	35	А





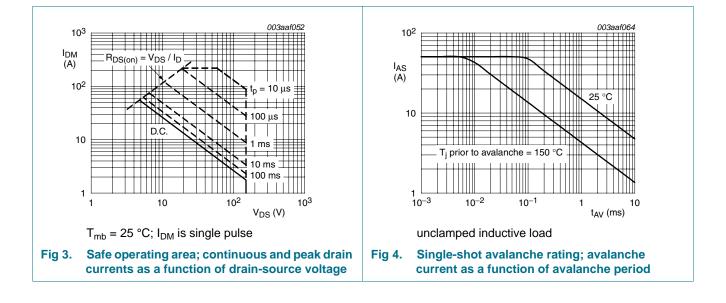


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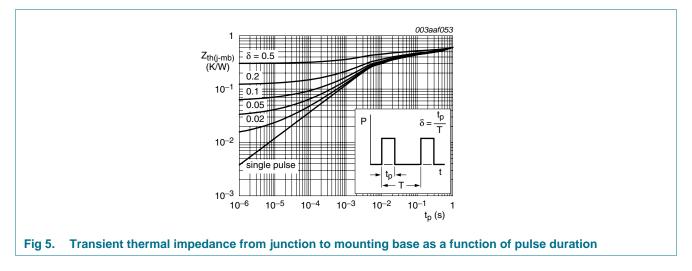


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5. Thermal characteristics

Table 5.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base		-	-	0.6	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	-	60	-	K/W



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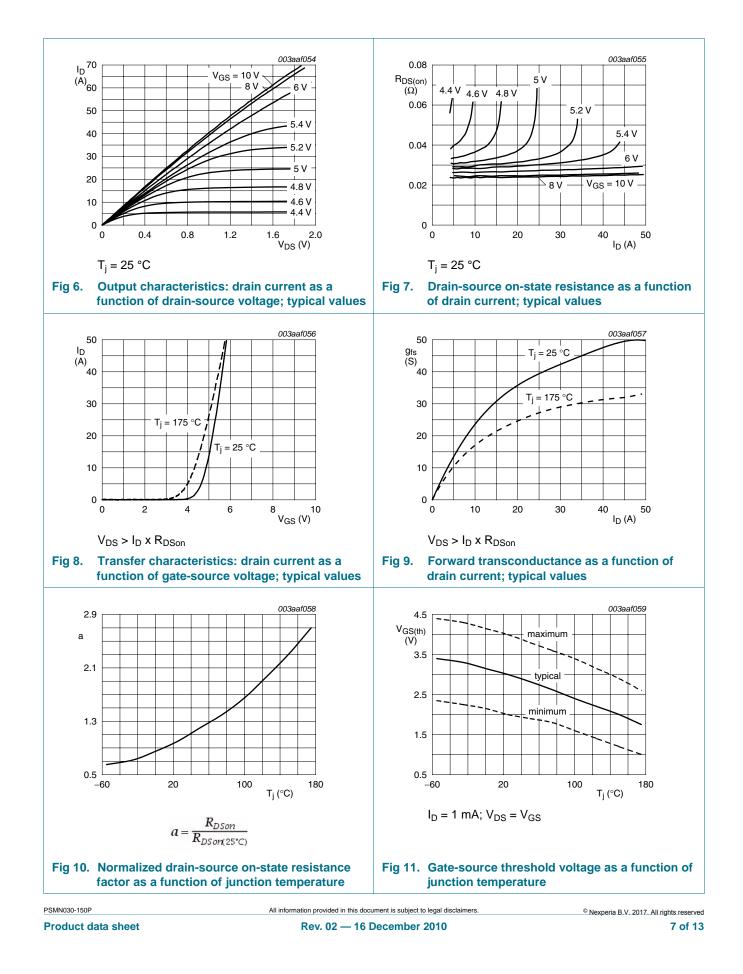
6. Characteristics

Table 6.	Characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Static cha	aracteristics					
V _{(BR)DSS}		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ °C}$	133	-	-	V
voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	150	-	-	V	
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C}$	-	-	6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	2	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C}$	1	-	-	V
I _{DSS}	drain leakage current	$V_{DS} = 150 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.05	10	μΑ
		V_{DS} = 150 V; V_{GS} = 0 V; T_j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	2	100	nA
		V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	V_{GS} = 10 V; I_D = 25 A; T_j = 175 °C	-	-	81	mΩ
	resistance	$V_{GS} = 10 \text{ V}; \text{ I}_D = 25 \text{ A}; \text{ T}_j = 25 ^\circ\text{C}$	-	24	30	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 55.5 \text{ A}; V_{DS} = 120 \text{ V};$ $V_{GS} = 10 \text{ V}; T_j = 25 \text{ °C}$	-	98	-	nC
Q _{GS}	gate-source charge		-	16	-	nC
Q_{GD}	gate-drain charge		-	38	50	nC
C _{iss}	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; \text{ f} = 1 \text{ MHz};$	-	3680	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	470	-	pF
C _{rss}	reverse transfer capacitance		-	220	-	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 75 \text{ V}; \text{ R}_{L} = 1.5 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	18	-	ns
t _r	rise time	$R_{G(ext)} = 5.6 \ \Omega; \ T_j = 25 \ ^{\circ}C$	-	71	-	ns
t _{d(off)}	turn-off delay time		-	97	-	ns
t _f	fall time		-	76	-	ns
L _D	internal drain inductance	measured from tab to centre of die ; T_j = 25 $^\circ\text{C}$	-	3.5	-	nH
		measured from drain lead to centre of die (SOT78 package only) ; $T_j = 25 \text{ °C}$	-	4.5		nH
L _S	internal source inductance	measured from source lead to source bond pad ; $T_j = 25 \text{ °C}$	-	7.5	-	nH
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_{S} = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_{j} = 25 \text{ °C}$	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s};$	-	109	-	ns
Q _r	recovered charge	$V_{GS} = 0 \text{ V}; V_{DS} = 30 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	610	-	nC

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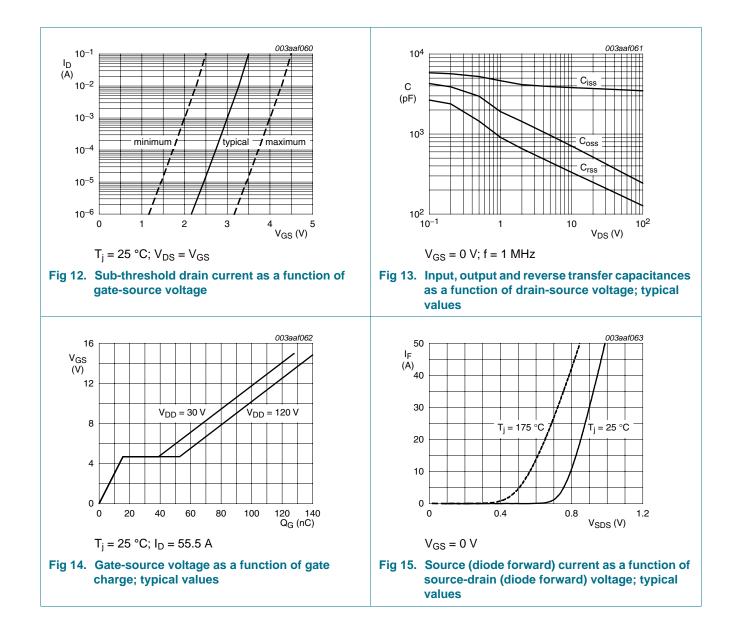
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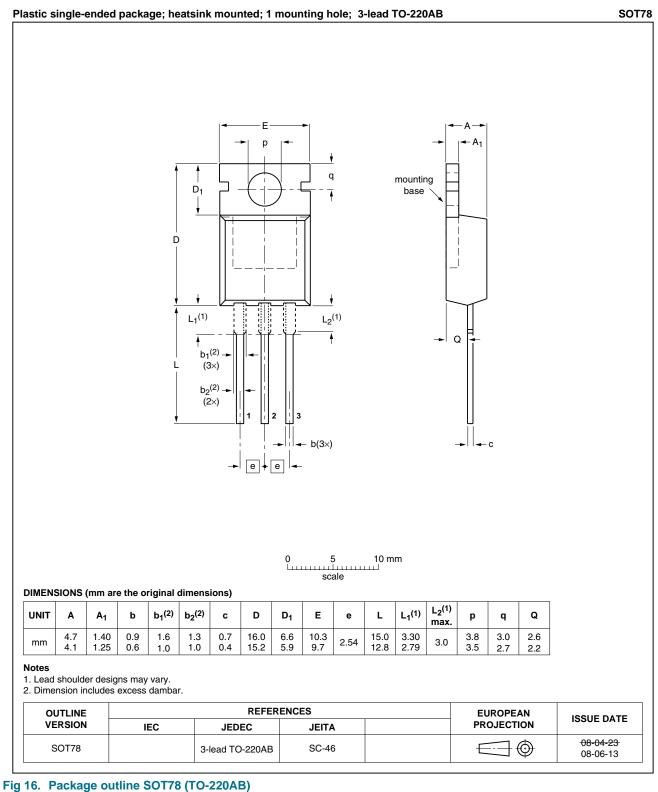
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Package outline 7.



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8. Revision history

Table 7. Revision I	nistory			
Document ID	Release date	Data sheet status	Change notice	Supersedes
PSMN030-150P v.2	20101216	Product data sheet	-	PSMN030-150P v.1
Modifications:	 The format of of NXP Semic 	this data sheet has been rec conductors.	designed to comply with	the new identity guidelines
	 Legal texts hat 	ve been adapted to the new	company name where	appropriate.
PSMN030-150P v.1	20000601	Product specification	-	-

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <u>http://www.nexperia.com</u>.

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